- **Qualified for Automotive Applications**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Output Swing Includes Both Supply Rails**
- **Extended Common-Mode Input Voltage Range . . . 0 V to 4.5 V (Min) with 5-V Single Supply**
- **No Phase Inversion**
- **Low Noise . . . 18 nV/√Hz Typ at f = 1 kHz**
- **Low Input Offset Voltage 950 μV Max at T_A = 25°C (TLV243xA)**
- **Low Input Bias Current . . . 1 pA Typ**
- **Very Low Supply Current . . . 125 μA Per Channel Max**
- **600-Ω Output Drive**
- **Macromodel Included**

description

The TLV243x and TLV243xA are low-voltage operational amplifier from Texas Instruments. The common-mode input voltage range for each device is extended over the typical CMOS amplifiers making them suitable for a wide range of applications. In addition, these devices do not phase invert when the common-mode input is driven to the supply rails. This satisfies most design requirements without paying a premium for rail-to-rail input performance. They also exhibit rail-to-rail output performance for increased dynamic range in single- or split-supply applications. This family is fully characterized at 3-V and 5-V supplies and is optimized for low-voltage operation. The TLV243x only requires 100 μA (typ) of supply current per channel, making it ideal for battery-powered applications. The TLV243x also has increased output drive over previous rail-to-rail operational amplifiers and can drive 600-Ω loads for telecom applications.

HIGH-LEVEL OUTPUT VOLTAGE vs HIGH-LEVEL OUTPUT CURRENT

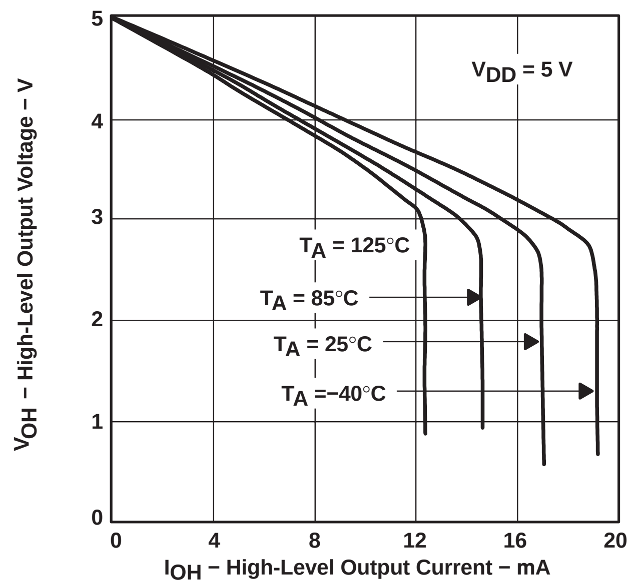


Figure 1

The other members in the TLV243x family are the high-power, TLV244x, and micro-power, TLV2422, versions.

The TLV243x, exhibiting high input impedance and low noise, is excellent for small-signal conditioning for high-impedance sources, such as piezoelectric transducers. Because of the micropower dissipation levels and low-voltage operation, these devices work well in hand-held monitoring and remote-sensing applications. In addition, the rail-to-rail output feature with single- or split-supplies makes this family a great choice when interfacing with analog-to-digital converters (ADCs). For precision applications, the TLV243xA is available and has a maximum input offset voltage of 950 μV.

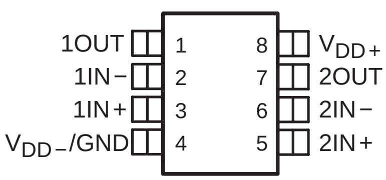
If the design requires single operational amplifiers, see the TI TLV2211/21/31. This is a family of rail-to-rail output operational amplifiers in the SOT-23 package. Their small size and low power consumption, make them ideal for high density, battery-powered equipment.

ORDERING INFORMATION†

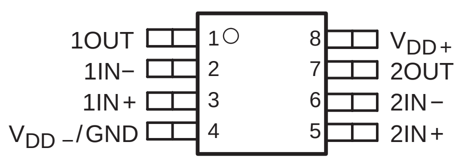
T_A	V_{IO}max AT 25°C	PACKAGE‡		ORDERABLE PART NUMBER	TOP-SIDE MARKING
−40°C to 125°C	950 µV	SOIC (D)	Tape and reel	TLV2432AQDRQ1	2432AQ
		TSSOP (PW)	Tape and reel	TLV2432AQPWRQ1§	
	2.5 mV	SOIC (D)	Tape and reel	TLV2432QDRQ1	2432Q1
		TSSOP (PW)	Tape and reel	TLV2432QPWRQ1§	
−40°C to 125°C	950 µV	SOIC (D)	Tape and reel	TLV2434AQDRQ1§	
		TSSOP (PW)	Tape and reel	TLV2434AQPWRQ1§	
	2.5 mV	SOIC (D)	Tape and reel	TLV2434QDRQ1§	
		TSSOP (PW)	Tape and reel	TLV2434QPWRQ1§	

† For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI web site at http://www.ti.com.
‡ Package drawings, thermal data, and symbolization are available at http://www.ti.com/packaging.
§ Product Preview.

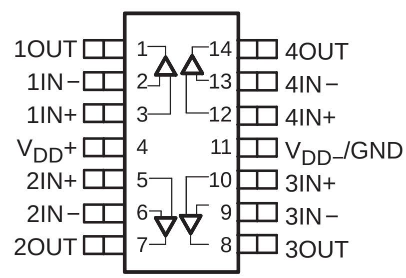
TLV2432
D PACKAGE
(TOP VIEW)



TLV2432
PW PACKAGE
(TOP VIEW)

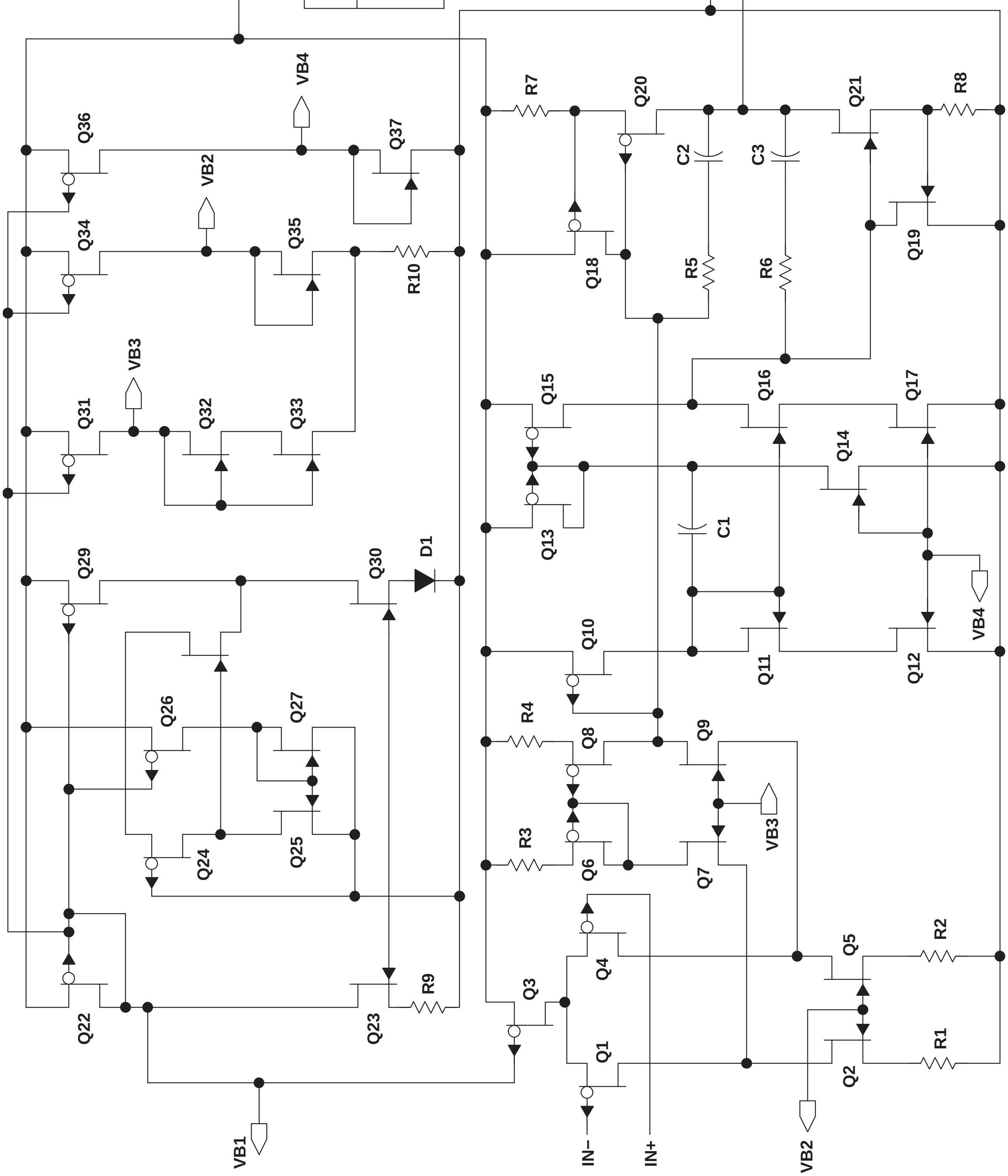


TLV2434
D OR PW PACKAGE
(TOP VIEW)



equivalent schematic (each amplifier)

COMPONENT COUNT	
Transistors	69
Diodes	5
Resistors	26
Capacitors	6



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage, V_{DD} (see Note 1) . . . . 12 V
Differential input voltage, V_{ID} (see Note 2) . . . . $\pm V_{DD}$
Input current, I_I (each input) . . . . ±5 mA
Output current, I_O . . . . ±50 mA
Total current into V_{DD+} . . . . ±50 mA
Total current out of V_{DD-} . . . . ±50 mA
Duration of short-circuit current at (or below) 25°C (see Note 3) . . . . unlimited
Continuous total dissipation . . . . See Dissipation Rating Table
Operating free-air temperature range, T_A: Q suffix . . . . −40°C to 125°C
Storage temperature range, T_{stg} . . . . −65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds . . . . 260°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES:
1. All voltage values, except differential voltages, are with respect to the midpoint between V_{DD+} and V_{DD-}.
2. Differential voltages are at IN+ with respect to IN−. Excessive current flows if input is brought below V_{DD-} − 0.3 V.
3. The output may be shorted to either supply. Temperature and/or supply voltages must be limited to ensure that the maximum dissipation rating is not exceeded.

DISSIPATION RATING TABLE

PACKAGE	$T_A \leq 25°C$ POWER RATING	DERATING FACTOR ABOVE $T_A = 25°C$	$T_A = 70°C$ POWER RATING	$T_A = 85°C$ POWER RATING	$T_A = 125°C$ POWER RATING
D (8)	725 mW	5.8 mW/°C	464 mW	377 mW	145 mW
D (14)	1022 mW	7.6 mW/°C	900 mW	777 mW	450 mW
PW (8)	525 mW	4.2 mW/°C	336 mW	273 mW	105 mW
PW (14)	720 mW	5.6 mW/°C	634 mW	547 mW	317 mW

recommended operating conditions

	MIN	MAX	UNIT
Supply voltage, V_{DD}	2.7	10	V
Input voltage range, V_I	V_{DD-}	V_{DD+} −0.8	V
Common-mode input voltage, V_{IC}	V_{DD-}	V_{DD+} −0.8	V
Operating free-air temperature, T_A	−40	125	°C

electrical characteristics at specified free-air temperature, V_{DD} = 3 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS		T_A†	TLV243x-Q1 MIN	TYP	MAX	UNIT
V_{IO}	Input offset voltage	V_{IC} = 0, V_O = 0, $V_{DD}\pm$ = ±1.5 V, R_S = 50 Ω	TLV243x	25°C		300	2000	µV
				Full range			2500	
			TLV243xA	25°C		300	950	
				Full range			2000	
α_{VIO}	Temperature coefficient of input offset voltage	V_{IC} = 0, V_O = 0,	$V_{DD}\pm$ = ±1.5 V, R_S = 50 Ω	25°C to 70°C		2		µV/°C
	Input offset voltage long-term drift (see Note 4)			25°C		0.003		µV/mo
I_{IO}	Input offset current			25°C		0.5		pA
				Full range			150	
I_{IB}	Input bias current			25°C		1		pA
				Full range			300	
V_{ICR}	Common-mode input voltage range	$\|V_{IO}\| \le$ 5 mV,	R_S = 50 Ω	25°C	0 to 2.5	−0.25 to 2.75		V
				Full range	0 to 2.2			
V_{OH}	High-level output voltage	I_{OH} = −100 µA		25°C		2.98		V
		I_{OH} = −3 mA		25°C		2.5		
				Full range	2.25			
V_{OL}	Low-level output voltage	V_{IC} = 1.5 V,	I_{OL} = 100 µA	25°C		0.02		V
		V_{IC} = 1.5 V,	I_{OL} = 3 mA	25°C		0.83		
				Full range			1	
A_{VD}	Large-signal differential voltage amplification	V_{IC} = 2.5 V, V_O = 1 V to 2 V	R_L = 2 kΩ‡	25°C	1.5	2.5		V/mV
				Full range	0.5			
			R_L = 1 MΩ‡	25°C		750		
$r_{i(d)}$	Differential input resistance			25°C		1000		GΩ
$r_{i(c)}$	Common-mode input resistance			25°C		1000		GΩ
$c_{i(c)}$	Common-mode input capacitance	f = 10 kHz		25°C		8		pF
z_o	Closed-loop output impedance	f = 100 kHz,	A_V = 10	25°C		130		Ω
CMRR	Common-mode rejection ratio	V_{IC} = V_{ICR} MIN, V_O = 1.5 V, R_S = 50 Ω		25°C	70	83		dB
				Full range	70			
k_{SVR}	Supply-voltage rejection ratio ($\Delta V_{DD}/\Delta V_{IO}$)	V_{DD} = 2.7 V to 8 V, V_{IC} = V_{DD}/2,	No load	25°C	80	95		dB
				Full range	80			
I_{DD}	Supply current	V_O = 1.5 V,	No load	25°C		195	250	µA
				Full range			260	

† Full range is −40°C to 125°C for Q level part.
‡ Referenced to 2.5 V

NOTE 4: Typical values are based on the input offset voltage shift observed through 500 hours of operating life test at T_A = 150°C extrapolated to T_A = 25°C using the Arrhenius equation and assuming an activation energy of 0.96 eV.

operating characteristics at specified free-air temperature, V_{DD} = 3 V

PARAMETER		TEST CONDITIONS		T_A†	TLV243x-Q1, TLV243xA-Q1 MIN	TYP	MAX	UNIT
SR	Slew rate at unity gain	V_O = 1 V to 2 V, C_L = 100 pF‡	R_L = 2 kΩ‡,	25°C	0.15	0.25		V/µs
				Full range	0.1			
V_n	Equivalent input noise voltage	f = 10 Hz		25°C		120		nV/√Hz
		f = 1 kHz		25°C		22		
$V_{N(PP)}$	Peak-to-peak equivalent input noise voltage	f = 0.1 Hz to 1 Hz		25°C		2.7		µV
		f = 0.1 Hz to 10 Hz		25°C		4		
I_n	Equivalent input noise current			25°C		0.6		fA√Hz
THD + N	Total harmonic distortion plus noise	V_O = 0.5 V to 2.5 V, f = 1 kHz, R_L = 2 kΩ‡	A_V = 1	25°C		0.065%		
			A_V = 10			0.5%		
	Gain-bandwidth product	f = 10 kHz, C_L = 100 pF‡	R_L = 2 kΩ‡,	25°C		0.5		MHz
B_{OM}	Maximum output-swing bandwidth	$V_{O(PP)}$ = 1 V, R_L = 2 kΩ‡,	A_V = 1, C_L = 100 pF‡	25°C		220		kHz
t_s	Settling time	A_V = −1, Step = 0.5 V to 2.5 V, R_L = 2 kΩ‡, C_L = 100 pF‡	To 0.1%	25°C		6.4		µs
			To 0.01%			14.1		
ϕ_m	Phase margin at unity gain	R_L = 2 kΩ‡,	C_L = 100 pF‡	25°C		62°		
	Gain margin			25°C		11		dB

† Full range is −40°C to 125°C for Q level part.
‡ Referenced to 2.5 V

electrical characteristics at specified free-air temperature, V_{DD} = 5 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS		T_A†	TLV243x-Q1 MIN	TYP	MAX	UNIT
V_{IO}	Input offset voltage	V_{IC} = 0, V_O = 0, $V_{DD}\pm$ = ±2.5 V, R_S = 50 Ω	TLV243x	25°C		300	2000	µV
				Full range			2500	
			TLV243xA	25°C		300	950	
				Full range			2000	
α_{VIO}	Temperature coefficient of input offset voltage	V_{IC} = 0, V_O = 0,	$V_{DD}\pm$ = ±2.5 V, R_S = 50 Ω	25°C to 70°C		2		µV/°C
	Input offset voltage long-term drift (see Note 4)			25°C		0.003		µV/mo
I_{IO}	Input offset current			25°C		0.5		pA
				Full range			150	
I_{IB}	Input bias current			25°C		1		pA
				Full range			300	
V_{ICR}	Common-mode input voltage range	$\lvert V_{IO}\rvert \le$ 5 mV,	R_S = 50 Ω	25°C	0 to 4.5	−0.25 to 4.75		V
				Full range	0 to 4.2			
V_{OH}	High-level output voltage	I_{OH} = −100 µA		25°C		4.97		V
		I_{OH} = −5 mA		25°C	4	4.35		
				Full range	4			
V_{OL}	Low-level output voltage	V_{IC} = 2.5 V,	I_{OL} = 100 µA	25°C		0.01		V
		V_{IC} = 2.5 V,	I_{OL} = 5 mA	25°C		0.8		
				Full range			1.25	
A_{VD}	Large-signal differential voltage amplification	V_{IC} = 2.5 V, V_O = 1 V to 4 V	R_L = 2 kΩ‡	25°C	2.5	3.8		V/mV
				Full range	0.5			
			R_L = 1 MΩ‡	25°C		950		
$r_{i(d)}$	Differential input resistance			25°C		1000		GΩ
$r_{i(c)}$	Common-mode input resistance			25°C		1000		GΩ
$c_{i(c)}$	Common-mode input capacitance	f = 10 kHz		25°C		8		pF
z_o	Closed-loop output impedance	f = 100 kHz,	A_V = 10	25°C		130		Ω
CMRR	Common-mode rejection ratio	V_{IC} = V_{ICR} MIN, V_O = 2.5 V, R_S = 50 Ω		25°C	70	90		dB
				Full range	70			
k_{SVR}	Supply-voltage rejection ratio ($\Delta V_{DD}/\Delta V_{IO}$)	V_{DD} = 4.4 V to 8 V, V_{IC} = V_{DD}/2,	No load	25°C	80	95		dB
				Full range	80			
I_{DD}	Supply current	V_O = 2.5 V,	No load	25°C		200	250	µA
				Full range			270	

† Full range is −40°C to 125°C for Q level part.
‡ Referenced to 2.5 V
NOTE 4: Typical values are based on the input offset voltage shift observed through 500 hours of operating life test at T_A = 150°C extrapolated to T_A = 25°C using the Arrhenius equation and assuming an activation energy of 0.96 eV.

operating characteristics at specified free-air temperature, V_{DD} = 5 V

PARAMETER		TEST CONDITIONS		T_A†	TLV243x-Q1, TLV243xA-Q1 MIN	TYP	MAX	UNIT
SR	Slew rate at unity gain	V_O = 1.5 V to 3.5 V, C_L = 100 pF‡	R_L = 2 kΩ‡,	25°C	0.15	0.25		V/μs
				Full range	0.1			
V_n	Equivalent input noise voltage	f = 10 Hz		25°C		100		nV/√Hz
		f = 1 kHz		25°C		18		
$V_{N(PP)}$	Peak-to-peak equivalent input noise voltage	f = 0.1 Hz to 1 Hz		25°C		1.9		μV
		f = 0.1 Hz to 10 Hz		25°C		2.8		
I_n	Equivalent input noise current			25°C		0.6		fA√Hz
THD + N	Total harmonic distortion plus noise	V_O = 1.5 V to 3.5 V, f = 1 kHz, R_L = 2 kΩ‡	A_V = 1	25°C		0.045%		
			A_V = 10			0.4%		
	Gain-bandwidth product	f = 10 kHz, C_L = 100 pF‡	R_L =2 kΩ‡,	25°C		0.55		MHz
B_{OM}	Maximum output-swing bandwidth	$V_{O(PP)}$ = 2 V, R_L = 2 kΩ‡,	A_V = 1, C_L = 100 pF‡	25°C		100		kHz
t_s	Settling time	A_V = −1, Step = 1.5 V to 3.5 V, R_L = 2 kΩ‡, C_L = 100 pF‡	To 0.1%	25°C		6.4		μs
			To 0.01%			13.1		
ϕ_m	Phase margin at unity gain	R_L = 2 kΩ‡,	C_L = 100 pF‡	25°C		66°		
	Gain margin			25°C		11		dB

† Full range is −40°C to 125°C for Q level part.
‡ Referenced to 2.5 V

TYPICAL CHARACTERISTICS

Table of Graphs

			FIGURE
V_{IO}	Input offset voltage	Distribution vs Common-mode input voltage	2,3 4,5
α_{VIO}	Temperature coefficient	Distribution	6,7
I_{IB}/I_{IO}	Input bias and input offset currents	vs Free-air temperature	8
V_{OH}	High-level output voltage	vs High-level output current	9,11
V_{OL}	Low-level output voltage	vs Low-level output current	10,12
$V_{O(PP)}$	Maximum peak-to-peak output voltage	vs Frequency	13
I_{OS}	Short-circuit output current	vs Supply voltage vs Free-air temperature	14 15
V_{ID}	Differential input voltage	vs Output voltage	16,17
	Differential gain	vs Load resistance	18
A_{VD}	Large-signal differential voltage amplification	vs Frequency	19,20
A_{VD}	Differential voltage amplification	vs Free-air temperature	21,22
z_o	Output impedance	vs Frequency	23,24
CMRR	Common-mode rejection ratio	vs Frequency vs Free-air temperature	25 26
k_{SVR}	Supply-voltage rejection ratio	vs Frequency vs Free-air temperature	27,28 29
I_{DD}	Supply current	vs Supply voltage	30
SR	Slew rate	vs Load capacitance vs Free-air temperature	31 32
V_O	Inverting large-signal pulse response		33,34
V_O	Voltage-follower large-signal pulse response		35,36
V_O	Inverting small-signal pulse response		37,38
V_O	Voltage-follower small-signal pulse response		39,40
V_n	Equivalent input noise voltage	vs Frequency	41, 42
	Noise voltage (referred to input)	Over a 10-second period	43
THD + N	Total harmonic distortion plus noise	vs Frequency	44,45
	Gain-bandwidth product	vs Free-air temperature vs Supply voltage	46 47
ϕ_m	Phase margin	vs Frequency vs Load capacitance	19,20 48
	Gain margin	vs Load capacitance	49
B_1	Unity-gain bandwidth	vs Load capacitance	50

TYPICAL CHARACTERISTICS

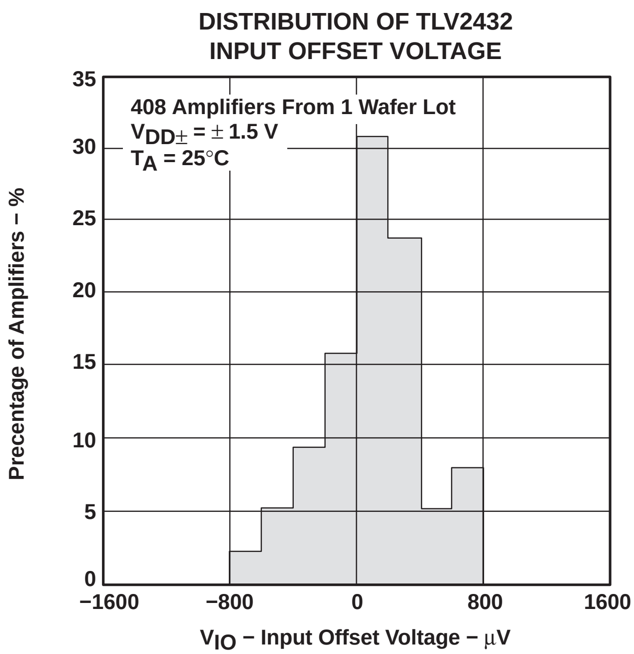


Figure 2

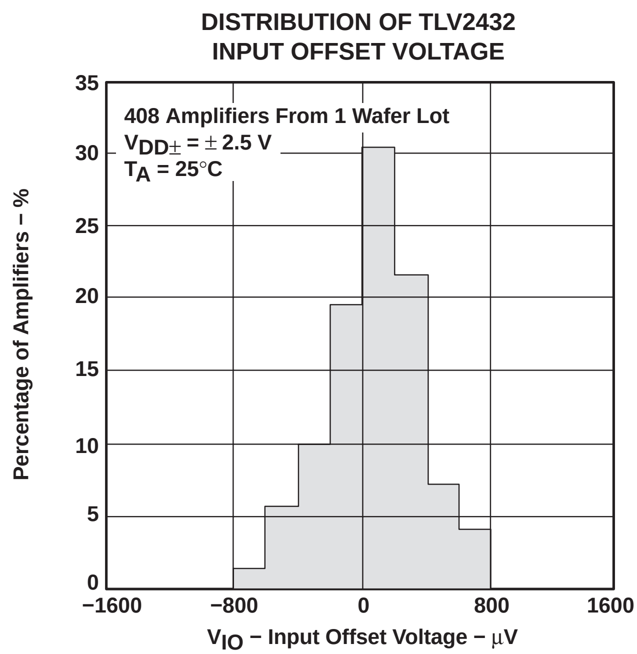


Figure 3

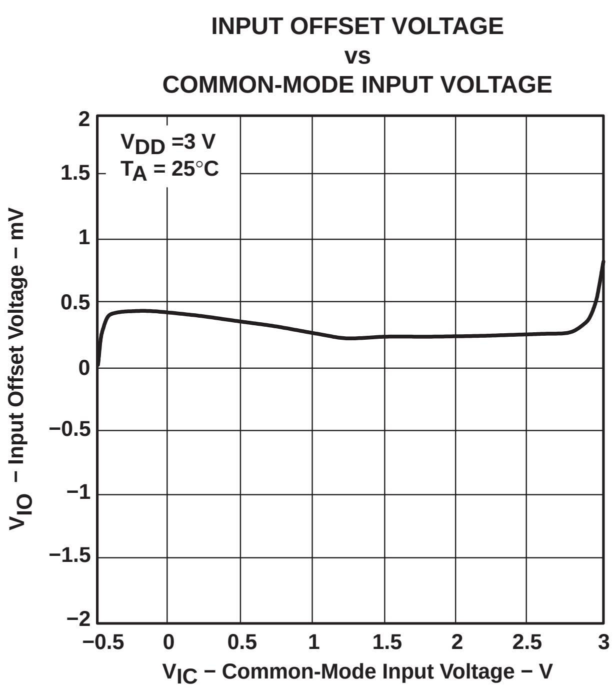


Figure 4

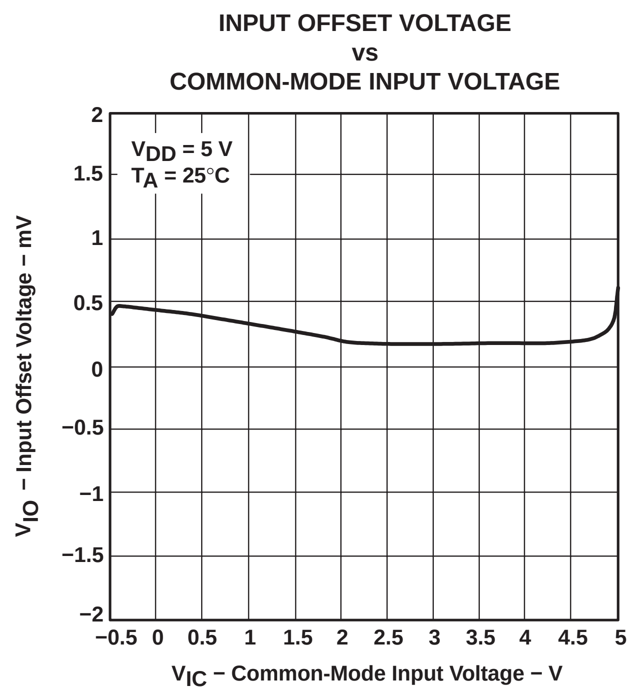


Figure 5

TYPICAL CHARACTERISTICS

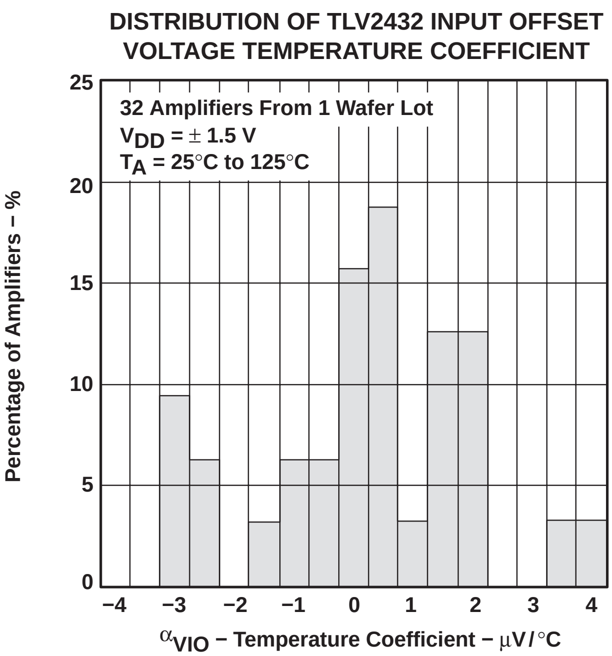


Figure 6

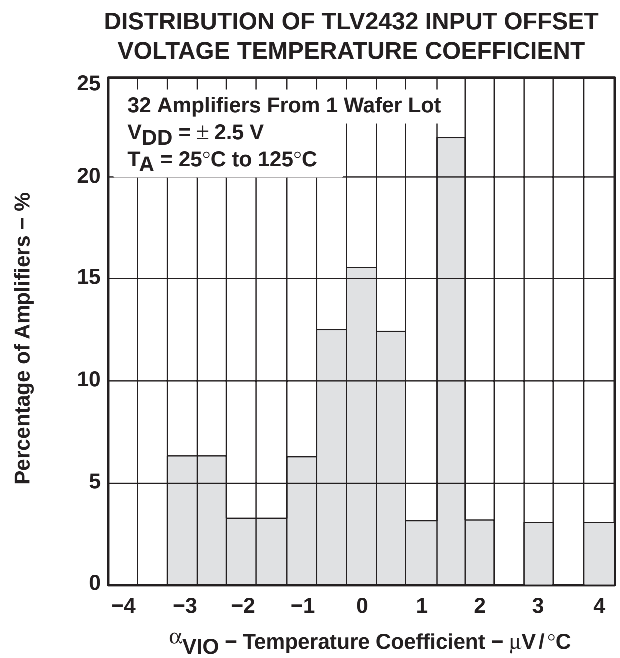


Figure 7

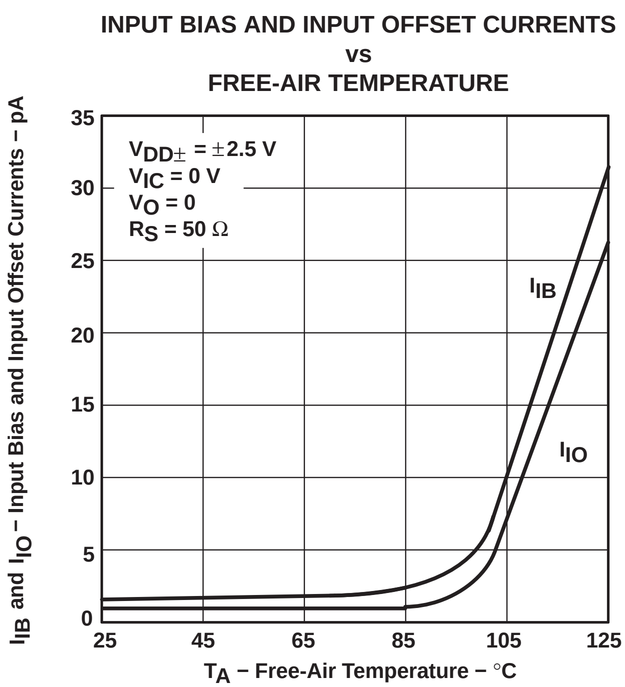


Figure 8

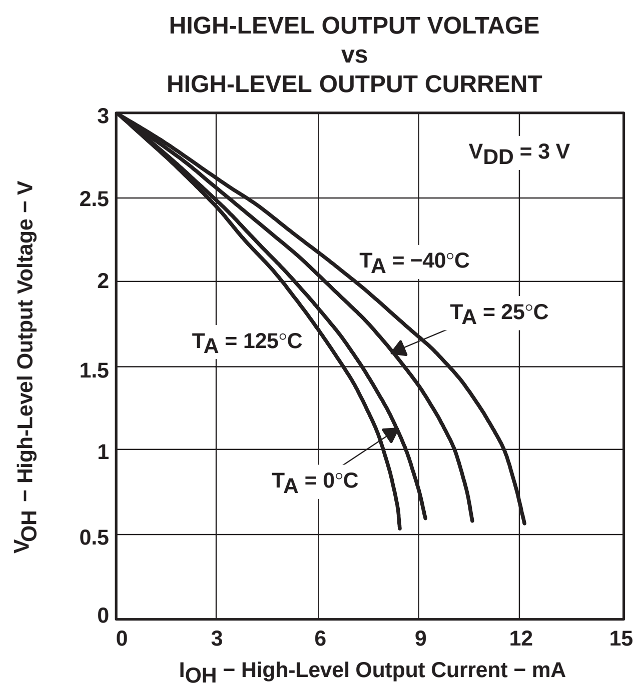


Figure 9

TYPICAL CHARACTERISTICS

LOW-LEVEL OUTPUT VOLTAGE
vs
LOW-LEVEL OUTPUT CURRENT

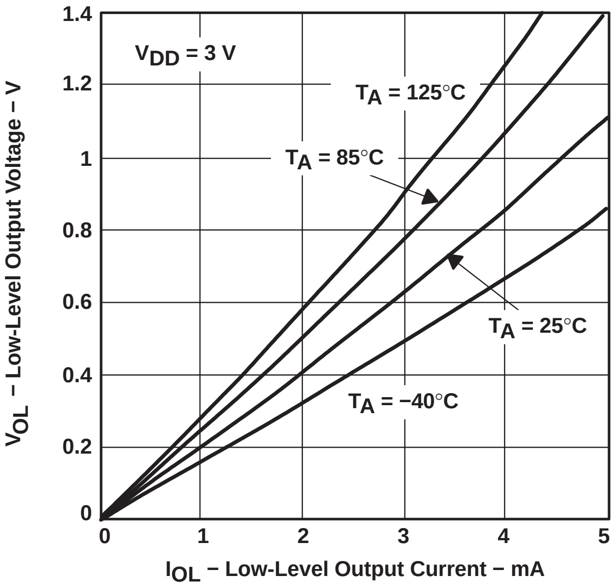


Figure 10

HIGH-LEVEL OUTPUT VOLTAGE
vs
HIGH-LEVEL OUTPUT CURRENT

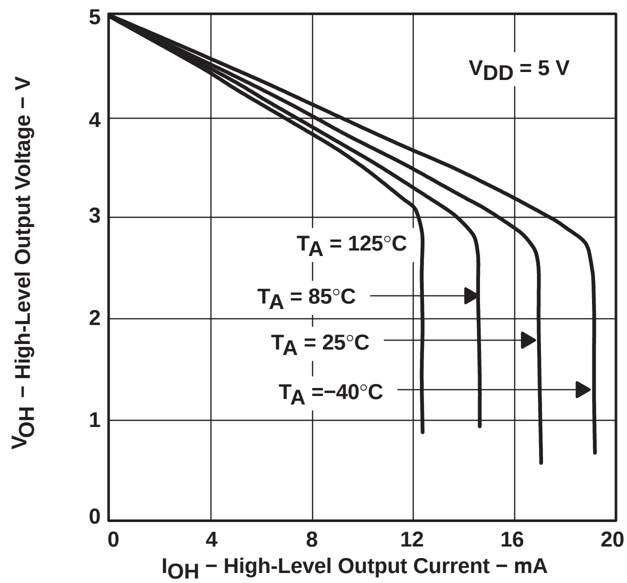


Figure 11

LOW-LEVEL OUTPUT VOLTAGE
vs
LOW-LEVEL OUTPUT CURRENT

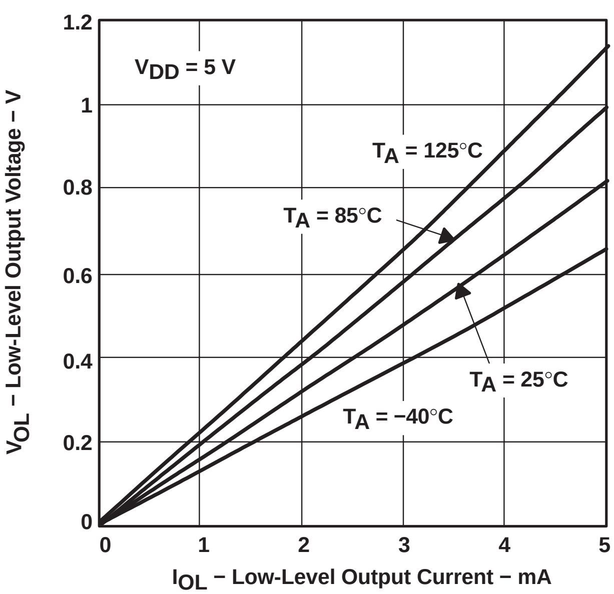


Figure 12

MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE
vs
FREQUENCY

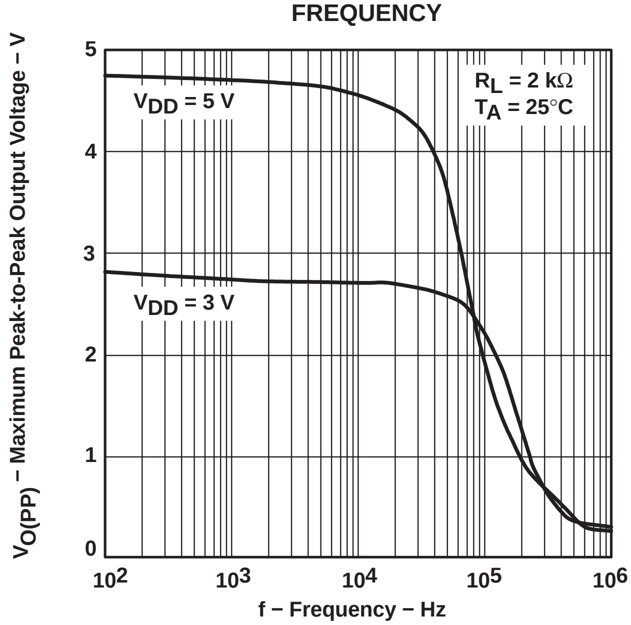


Figure 13

TYPICAL CHARACTERISTICS

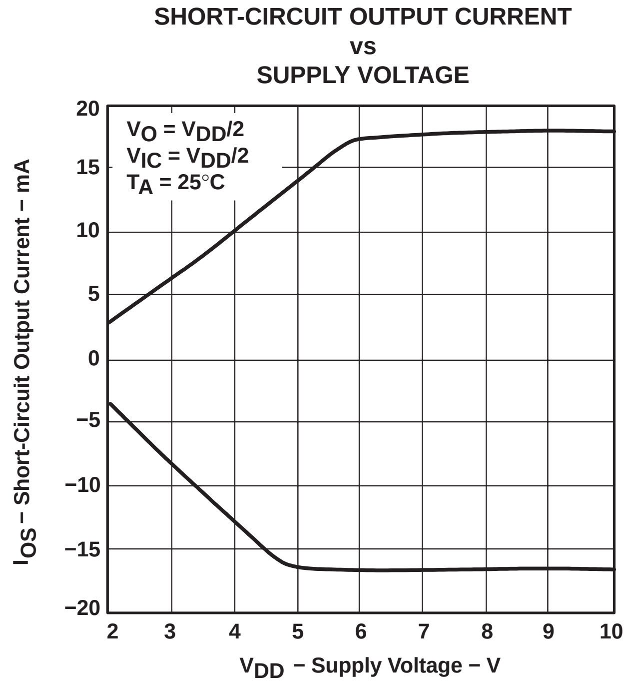


Figure 14

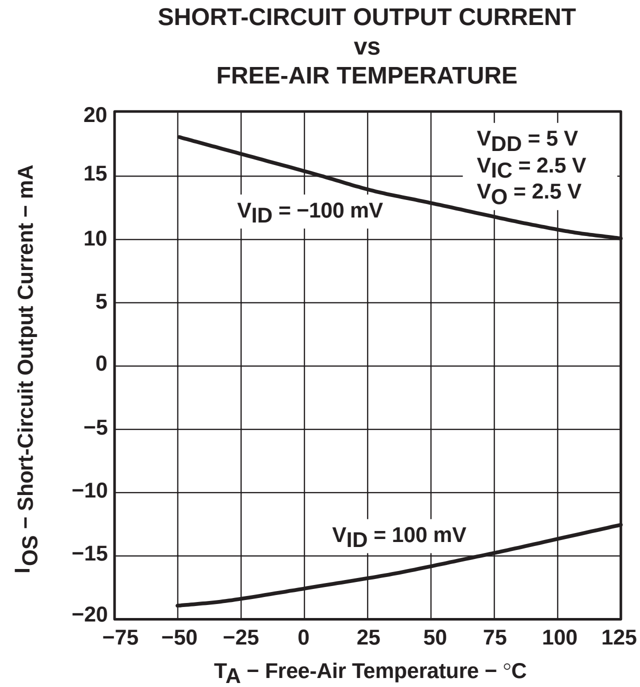


Figure 15

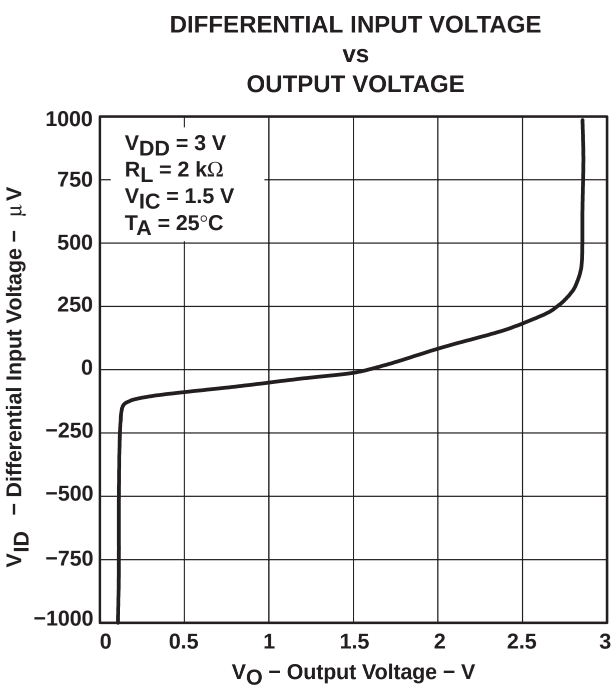


Figure 16

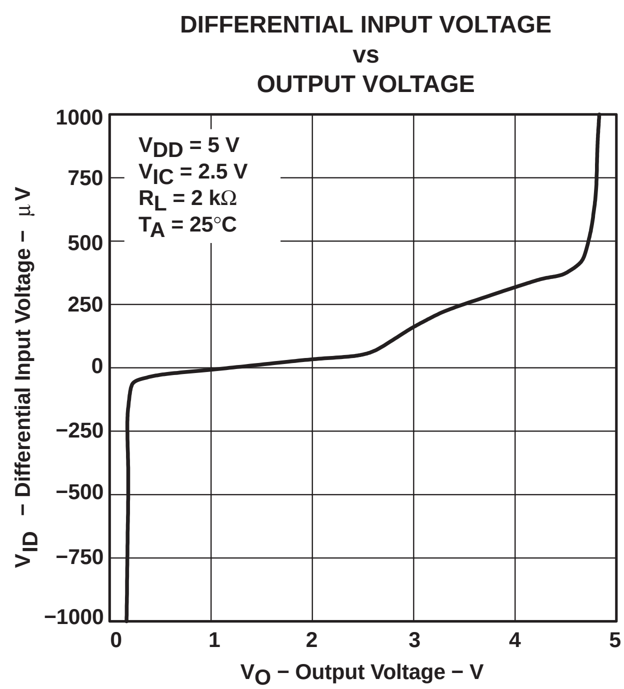


Figure 17

TYPICAL CHARACTERISTICS

DIFFERENTIAL GAIN
vs
LOAD RESISTANCE

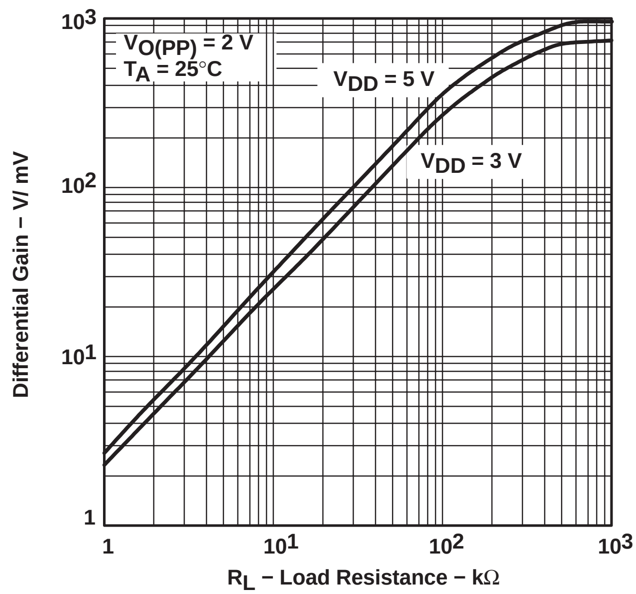


Figure 18

LARGE-SIGNAL DIFFERENTIAL VOLTAGE
AMPLIFICATION AND PHASE MARGIN
vs
FREQUENCY

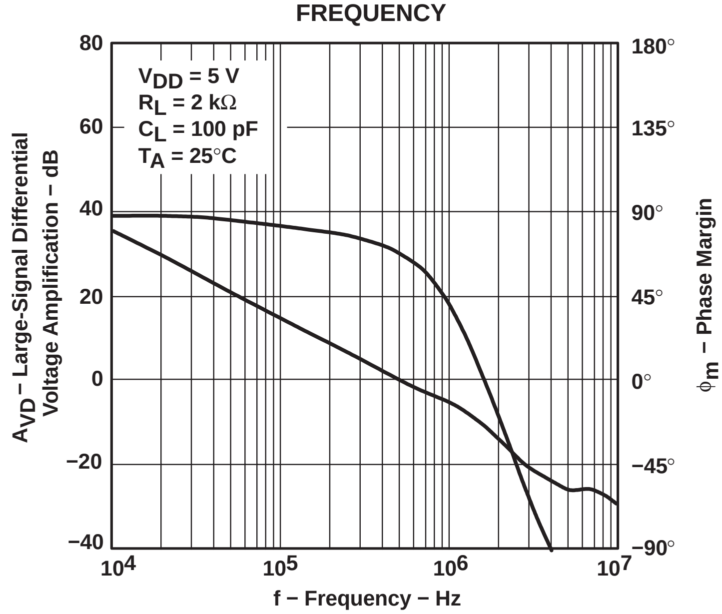


Figure 19

TYPICAL CHARACTERISTICS

LARGE-SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION AND PHASE MARGIN vs FREQUENCY

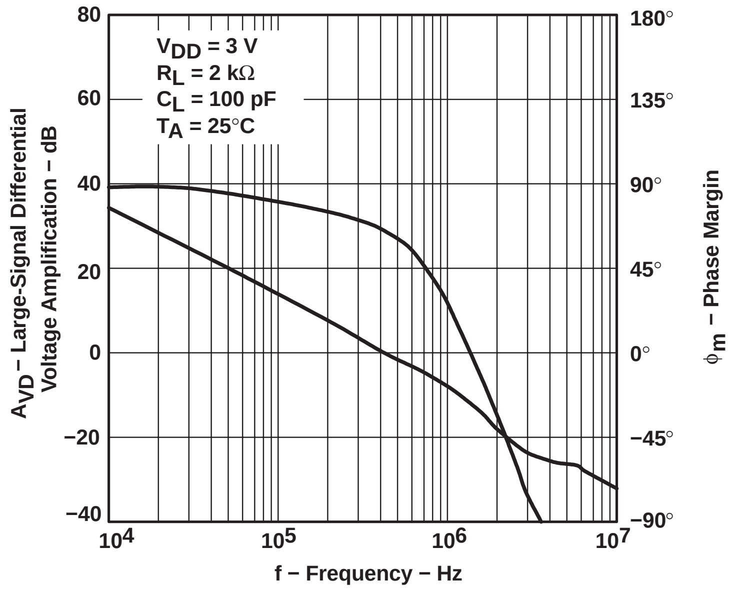


Figure 20

DIFFERENTIAL VOLTAGE AMPLIFICATION vs FREE-AIR TEMPERATURE

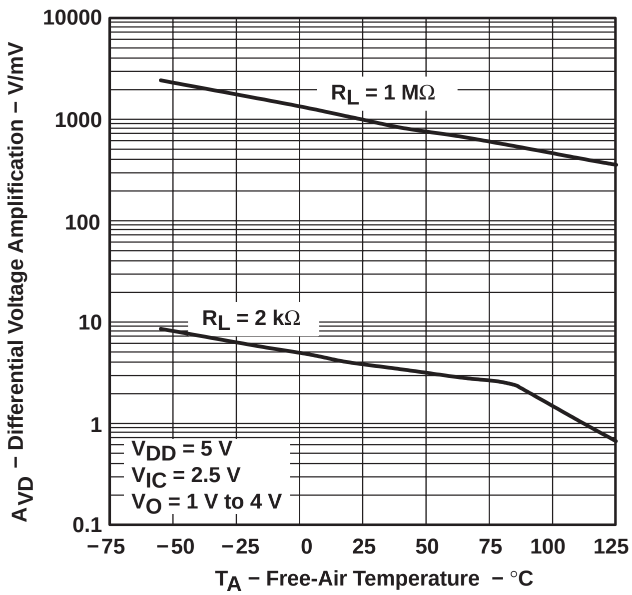


Figure 21

DIFFERENTIAL VOLTAGE AMPLIFICATION vs FREE-AIR TEMPERATURE

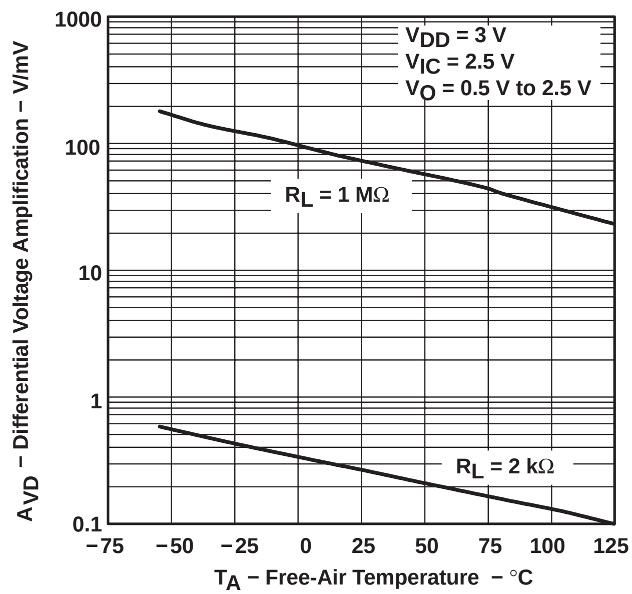


Figure 22

TYPICAL CHARACTERISTICS

OUTPUT IMPEDANCE
vs
FREQUENCY

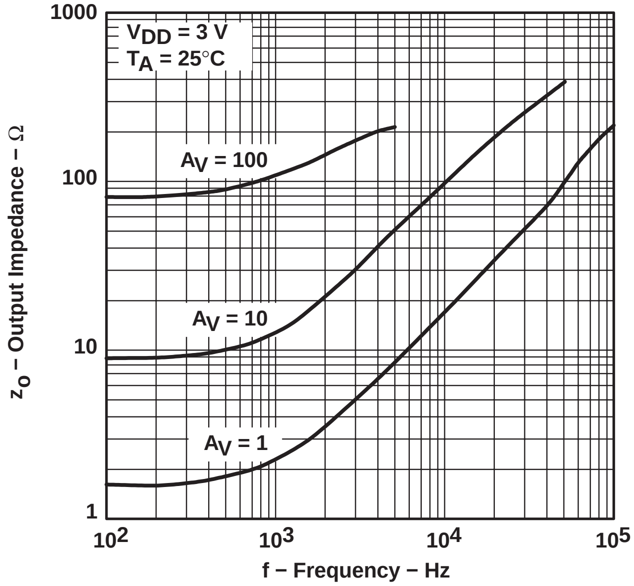


Figure 23

OUTPUT IMPEDANCE
vs
FREQUENCY

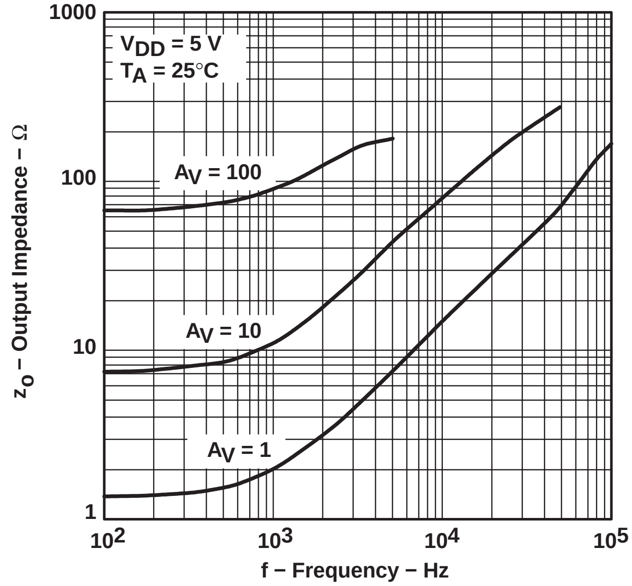


Figure 24

COMMON-MODE REJECTION RATIO
vs
FREQUENCY

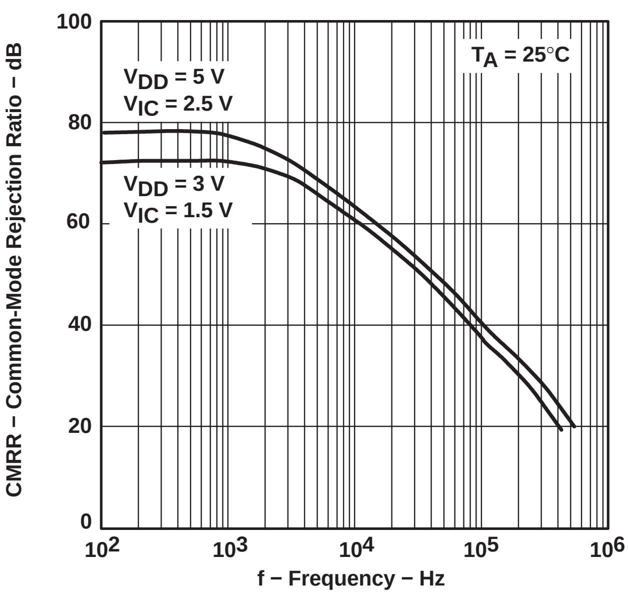


Figure 25

COMMON-MODE REJECTION RATIO
vs
FREE-AIR TEMPERATURE

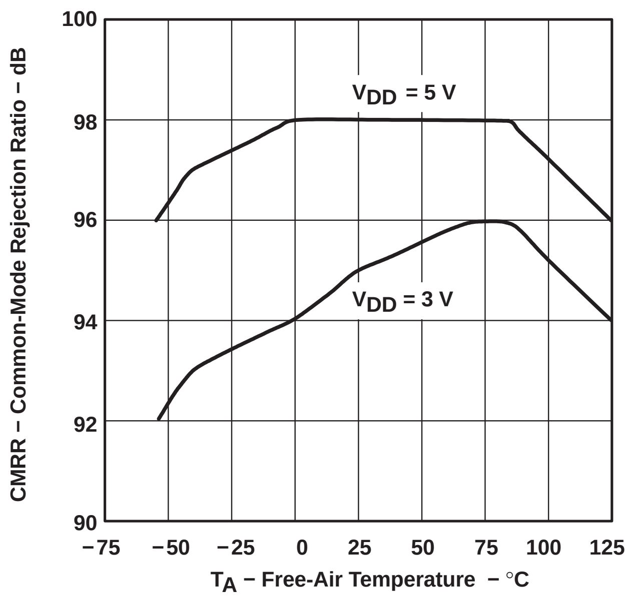
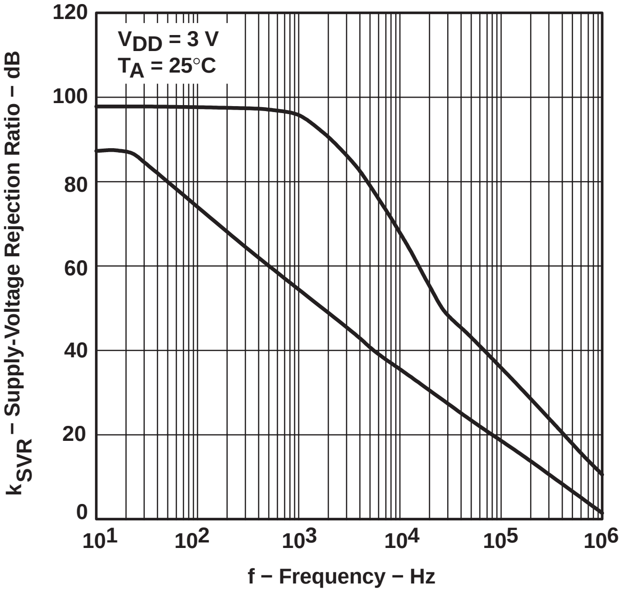


Figure 26

TYPICAL CHARACTERISTICS



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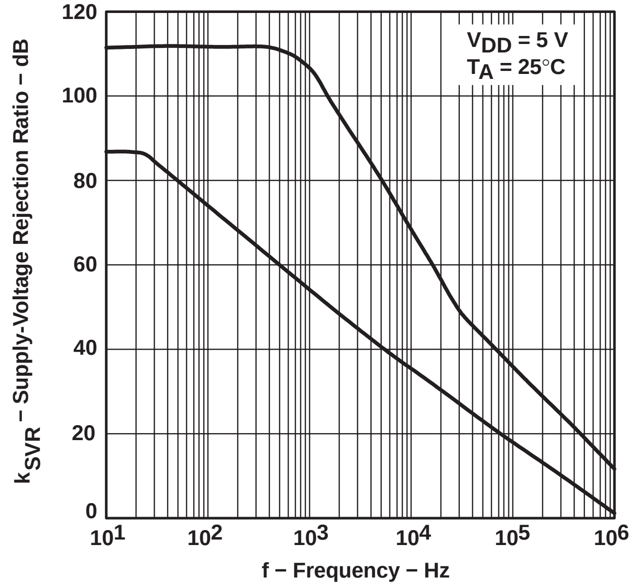

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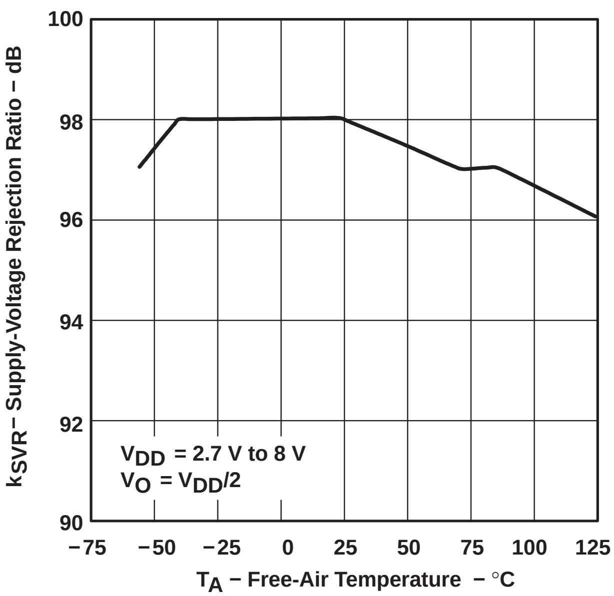

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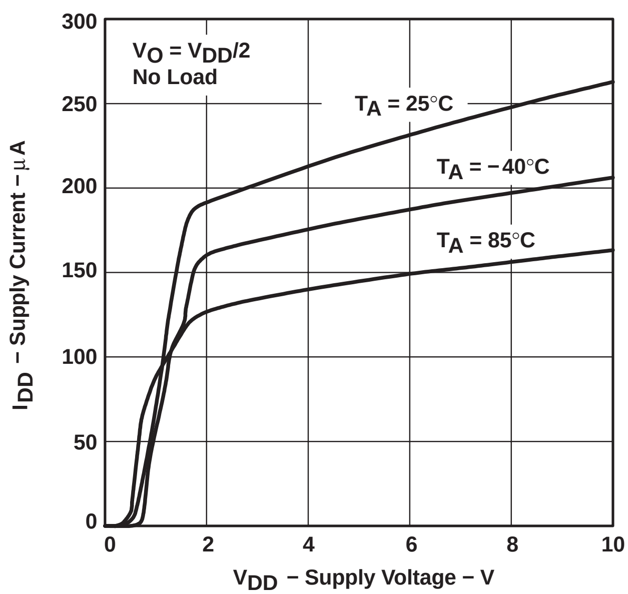
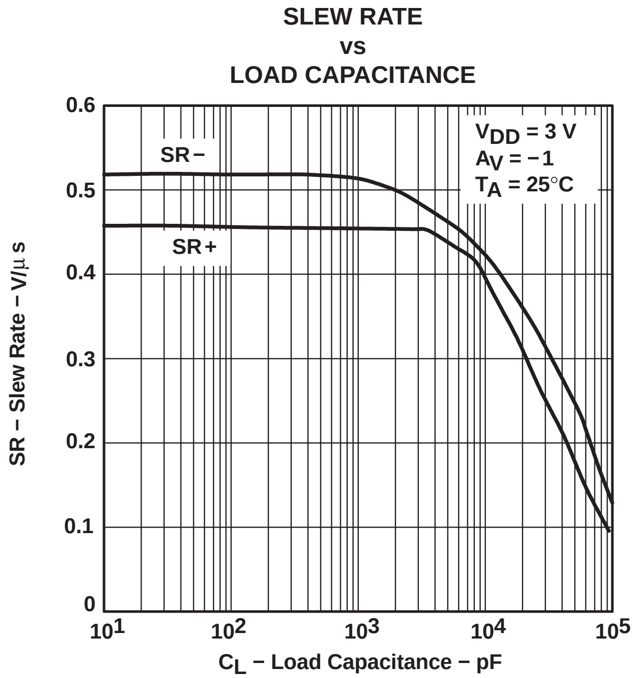


Figure 30

TYPICAL CHARACTERISTICS



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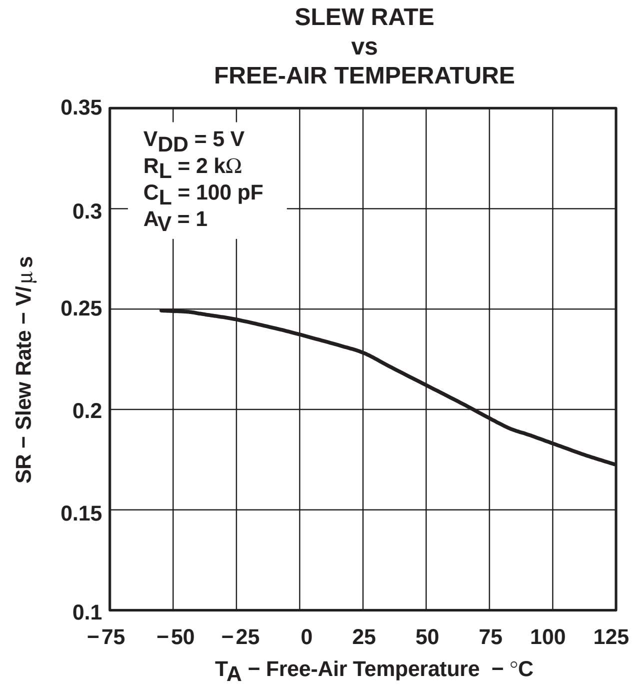

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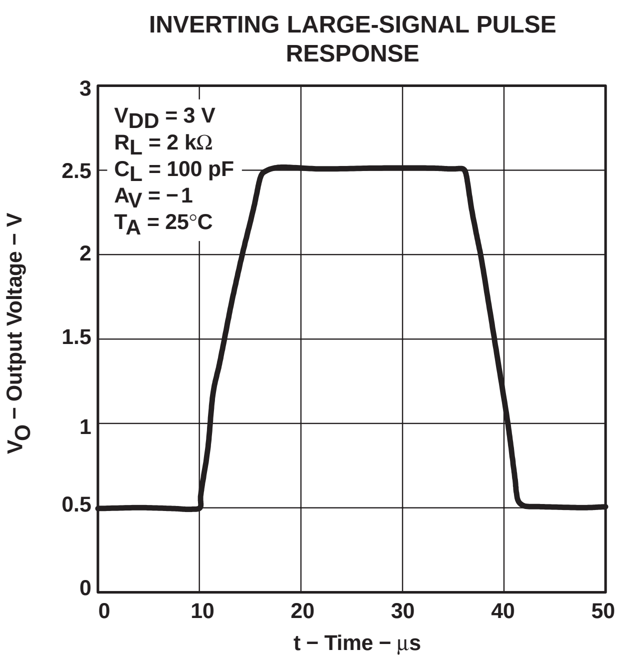

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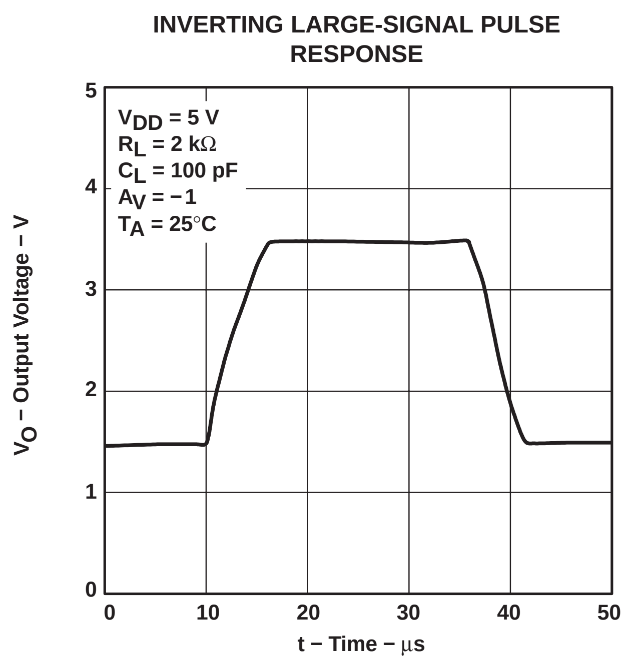
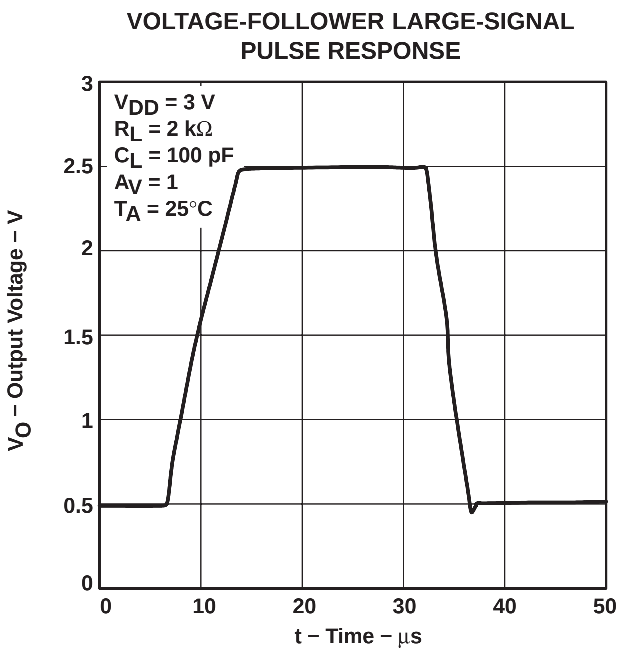


Figure 34

TYPICAL CHARACTERISTICS



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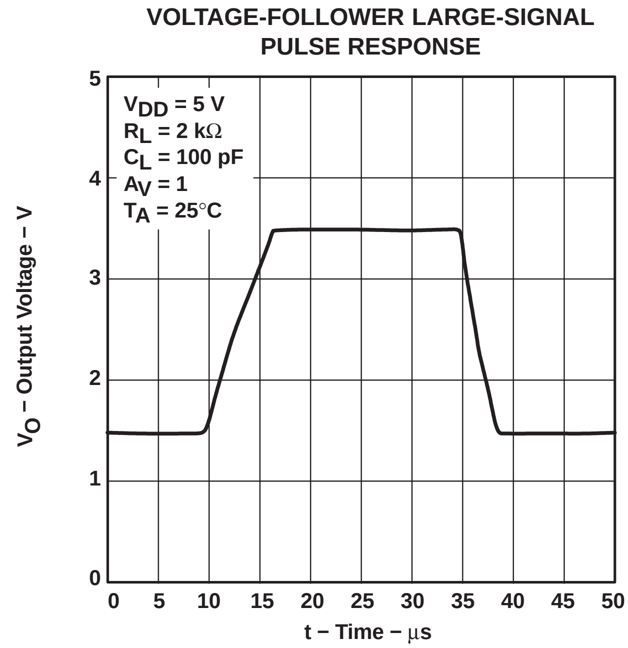

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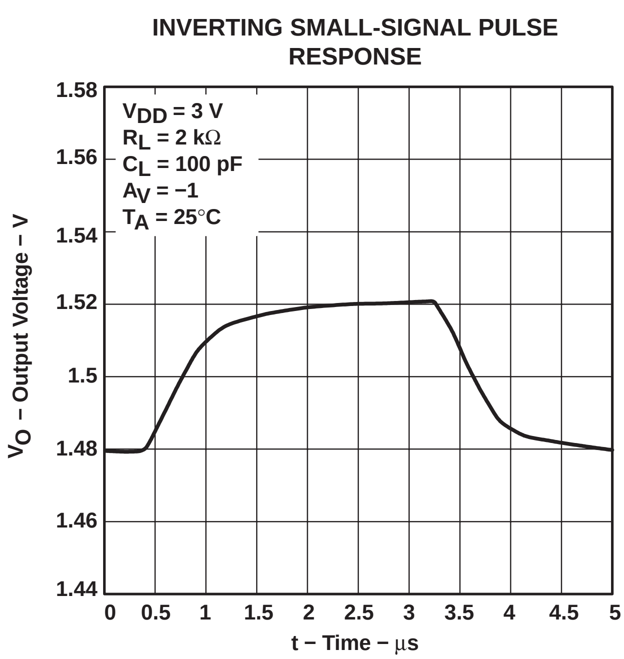

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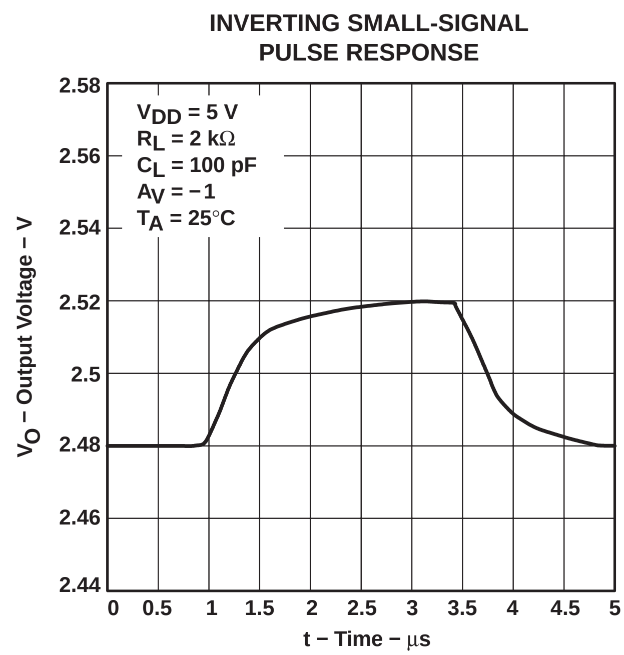
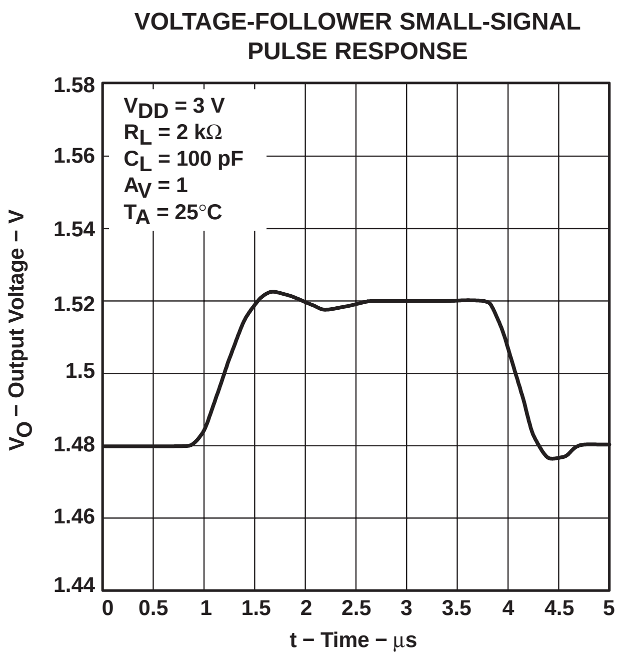


Figure 38

TYPICAL CHARACTERISTICS



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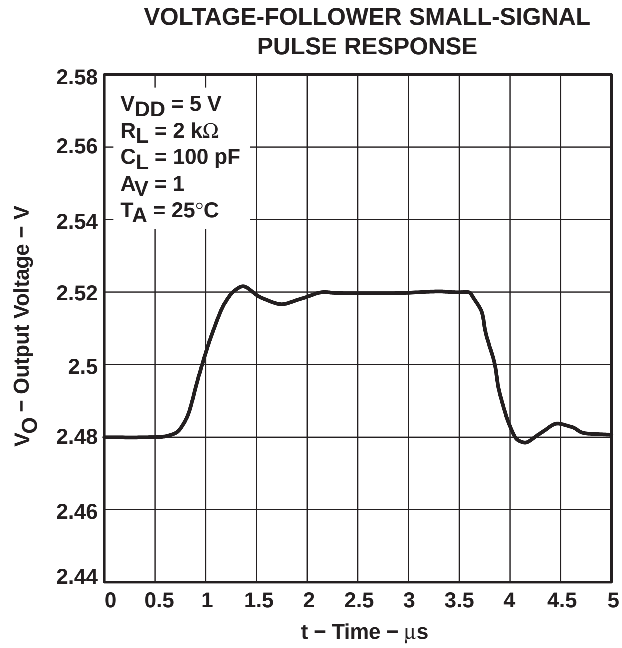

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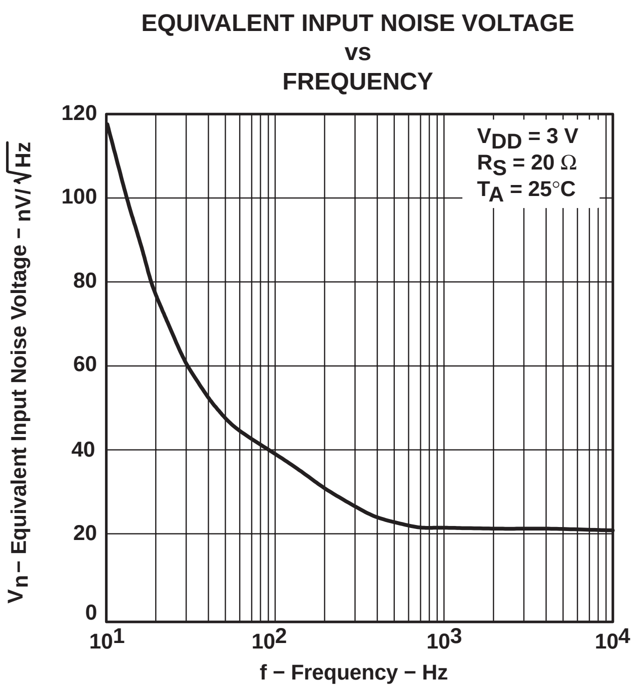

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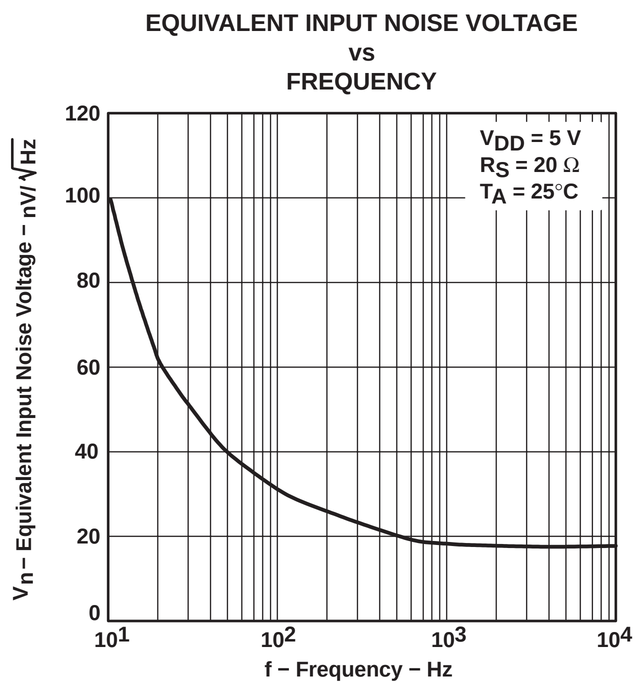
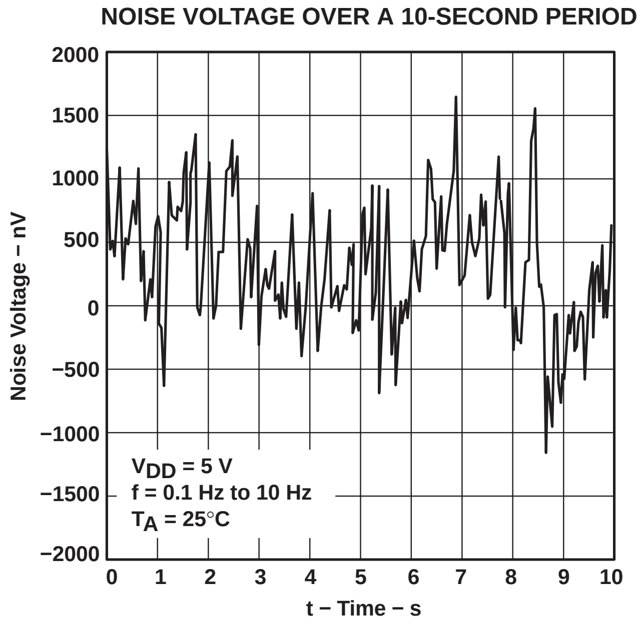


Figure 42

TYPICAL CHARACTERISTICS



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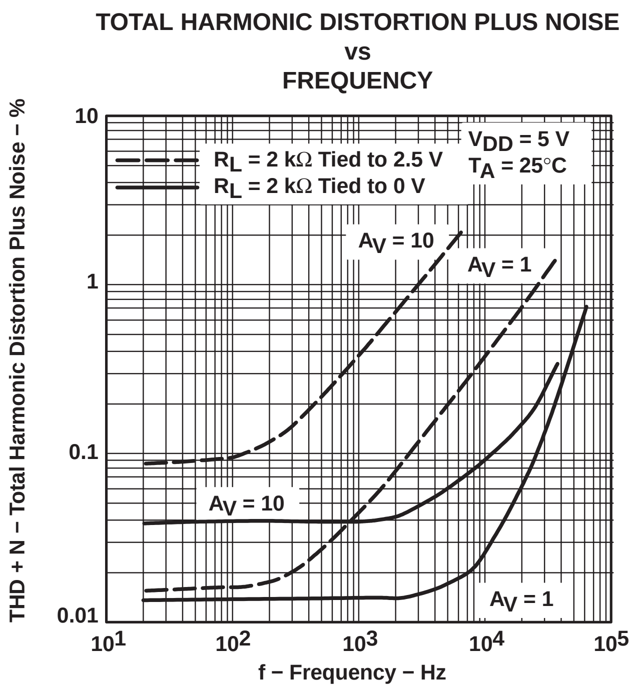

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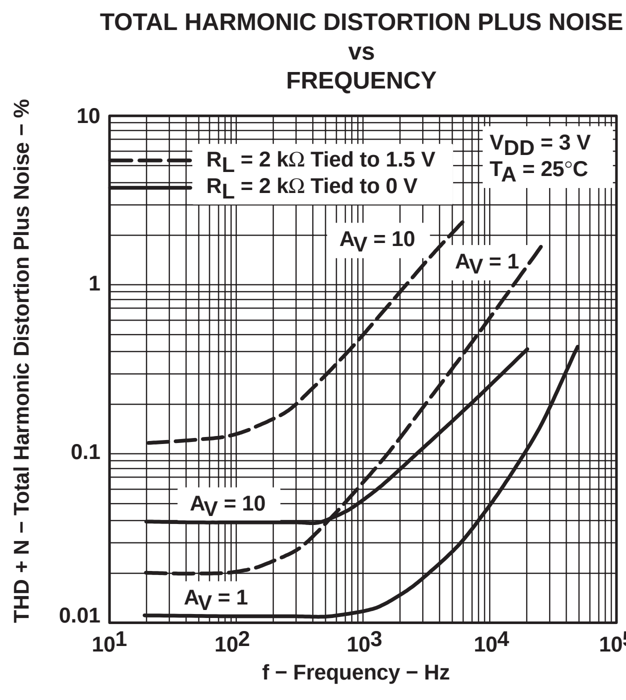
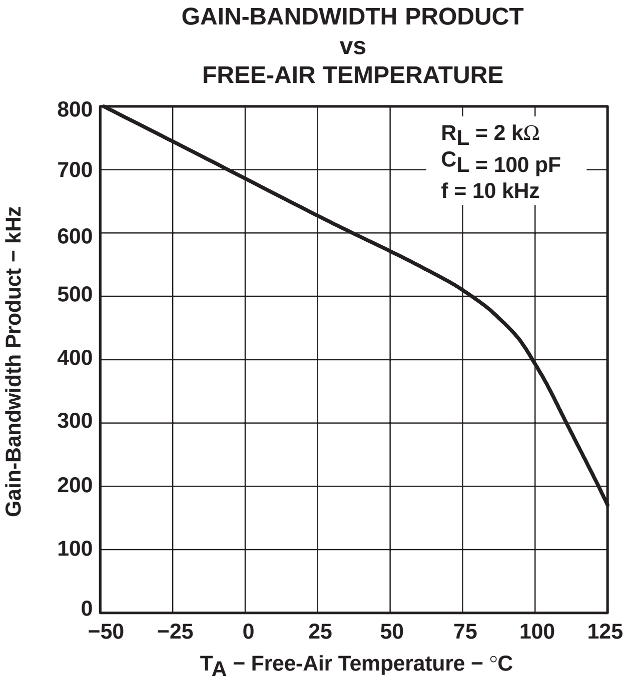


Figure 45

TYPICAL CHARACTERISTICS



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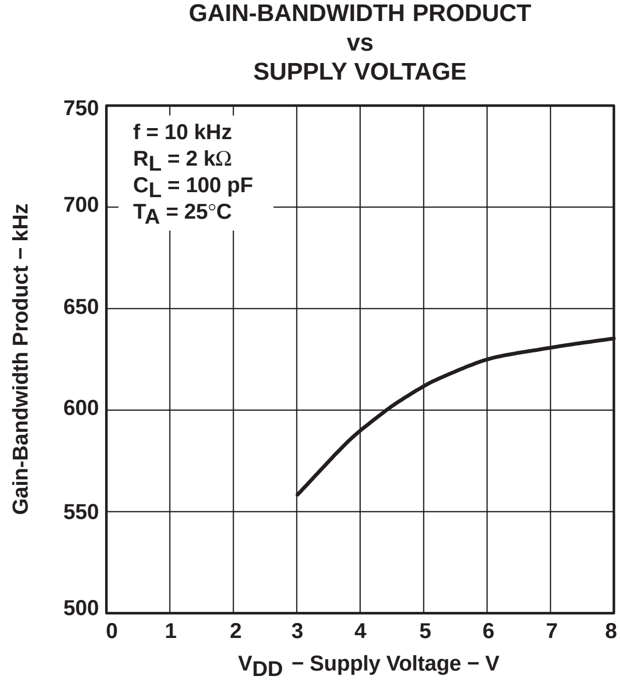

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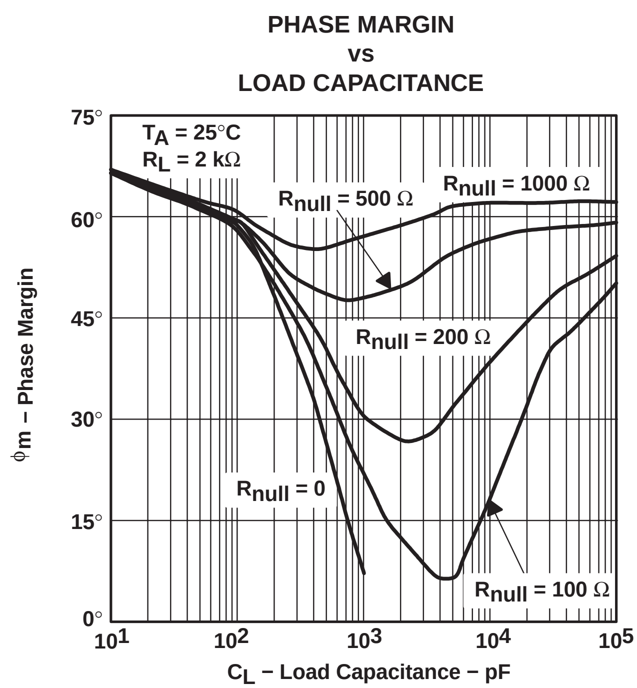

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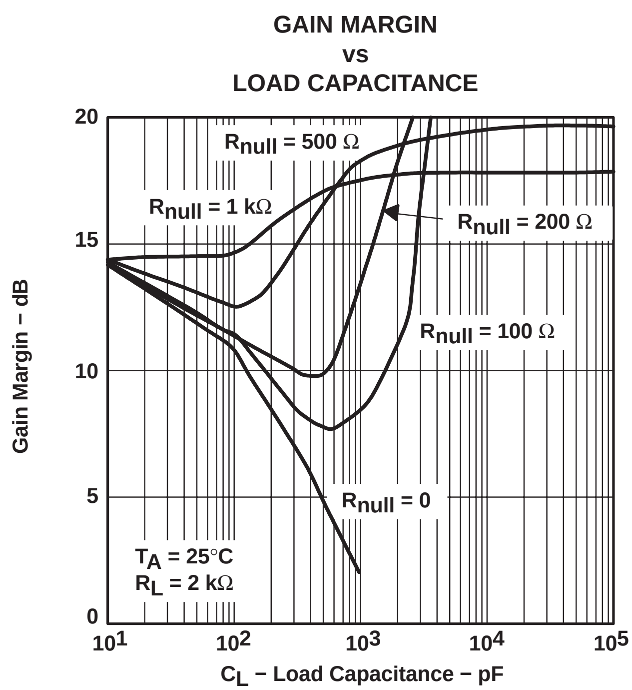


Figure 49

TYPICAL CHARACTERISTICS

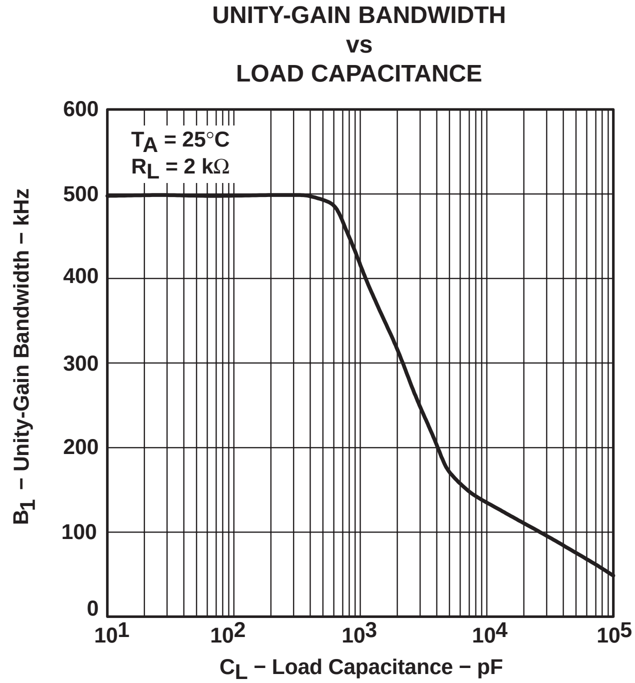


Figure 50

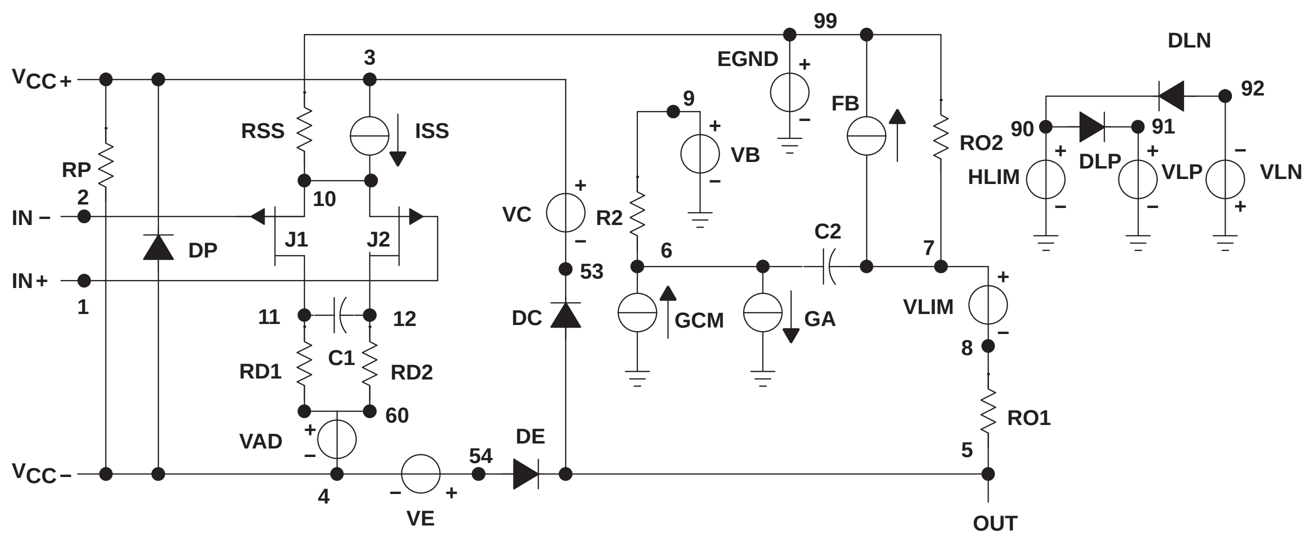
APPLICATION INFORMATION

macromodel information

Macromodel information provided was derived using Microsim *Parts*™, the model generation software used with Microsim *PSpice*™. The Boyle macromodel (see Note 5) and subcircuit in Figure 51 are generated using the TLV243x typical electrical and operating characteristics at T_A = 25°C. Using this information, output simulations of the following key parameters can be generated to a tolerance of 20% (in most cases):

- Maximum positive output voltage swing
- Maximum negative output voltage swing
- Slew rate
- Quiescent power dissipation
- Input bias current
- Open-loop voltage amplification
- Unity-gain frequency
- Common-mode rejection ratio
- Phase margin
- DC output resistance
- AC output resistance
- Short-circuit output current limit

NOTE 4: G. R. Boyle, B. M. Cohn, D. O. Pederson, and J. E. Solomon, “Macromodeling of Integrated Circuit Operational Amplifiers”, *IEEE Journal of Solid-State Circuits,* SC-9, 353 (1974).




```
.SUBCKT TLV2432 1 2 3 4 5
        C1     11    12    3.560E−12
        C2     6     7     15.00E−12
        DC     5     53    DX
        DE     54    5     DX
        DLP    90    91    DX
        DLN    92    90    DX
        DP     4     3     DX
        EGND   99    0     POLY (2) (3,0) (4,0) 0 .5 .5
        FB     7     99    POLY (5) VB VC VE VLP
        + VLN 0 21.04E6 −30E6 30E6 30E6 −30E6
        GA     6     0     11    12 47.12E−6
        GCM    0     6     10    99 4.9E−9
        ISS    3     10    DC 8.250E−6
        HLIM   90    0     VLIM 1K
        J1     11    2     10 JX
        J2     12    1     10 JX
        R2     6     9     100.0E3
RD1     60    11    21.22E3
RD2     60    12    21.22E3
R01     8     5     120
R02     7     99    120
RP      3     4     26.04E3
RSS     10    99    24.24E6
VAD     60    4     −.6
VB      9     0     DC 0
VC      3     53    DC .65
VE      54    4     DC .65
VLIM    7     8     DC 0
VLP     91    0     DC 1.4
VLN     0     92    DC 9.4
.MODEL DX D (IS=800.0E−18)
.MODEL JX PJF (IS=500.0E−15 BETA=281E−6
+ VTO=−.065)
.ENDS
```

Figure 51. Boyle Macromodel and Subcircuit

PSpice and *Parts* are trademarks of MicroSim Corporation.

PACKAGING INFORMATION

Orderable Device	Status [1]	Package Type	Package Drawing	Pins	Package Qty	Eco Plan [2]	Lead/Ball Finish	MSL Peak Temp [3]
TLV2432AQDRG4Q1	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLV2432AQDRQ1	ACTIVE	SOIC	D	8	2500	Pb-Free (RoHS)	CU NIPDAU	Level-2-250C-1 YEAR/ Level-1-235C-UNLIM
TLV2432QDRG4Q1	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLV2432QDRQ1	ACTIVE	SOIC	D	8	2500	Pb-Free (RoHS)	CU NIPDAU	Level-2-250C-1 YEAR/ Level-1-235C-UNLIM

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.
TBD: The Pb-Free/Green conversion plan has not been defined.
Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.
Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.
Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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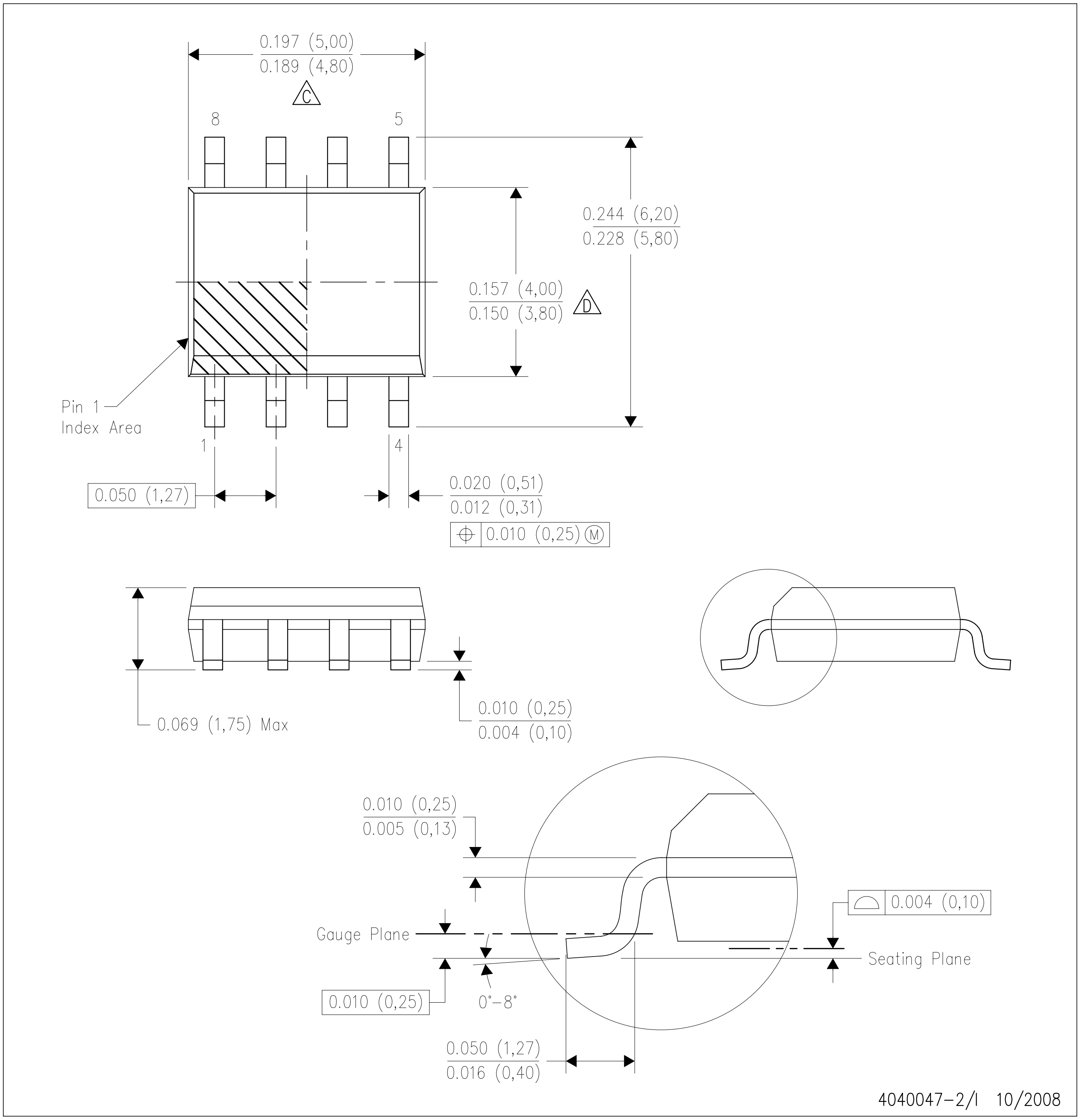
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF TLV2432-Q1, TLV2432A-Q1 :
- Catalog: TLV2432, TLV2432A
- Military: TLV2432M, TLV2432AM

NOTE: Qualified Version Definitions:
- Catalog - TI's standard catalog product
- Military - QML certified for Military and Defense Applications

D (R-PDSO-G8) PLASTIC SMALL-OUTLINE PACKAGE



NOTES:
- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 (0,15) per end.
- D. Body width does not include interlead flash. Interlead flash shall not exceed .017 (0,43) per side.
- E. Reference JEDEC MS-012 variation AA.